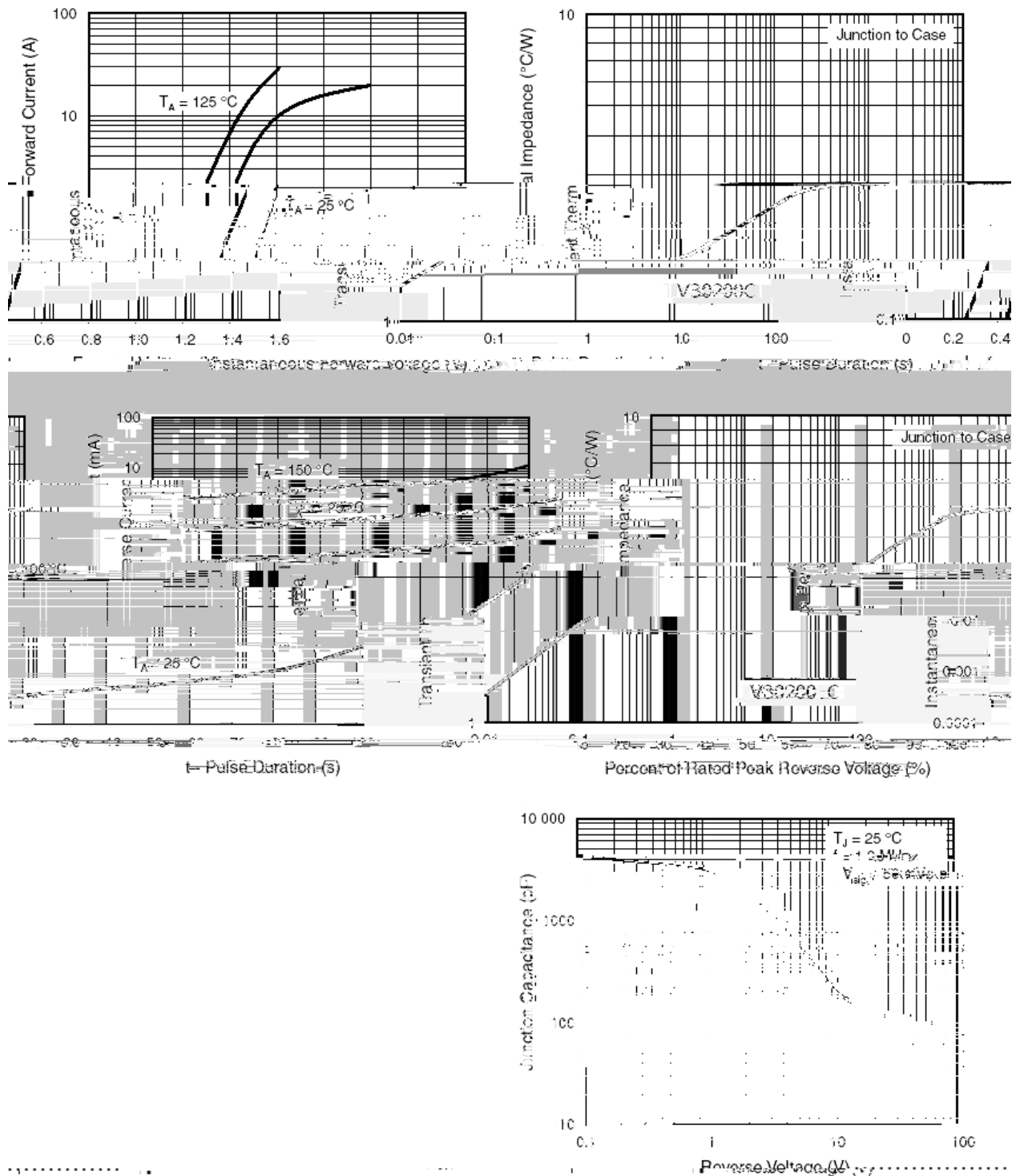


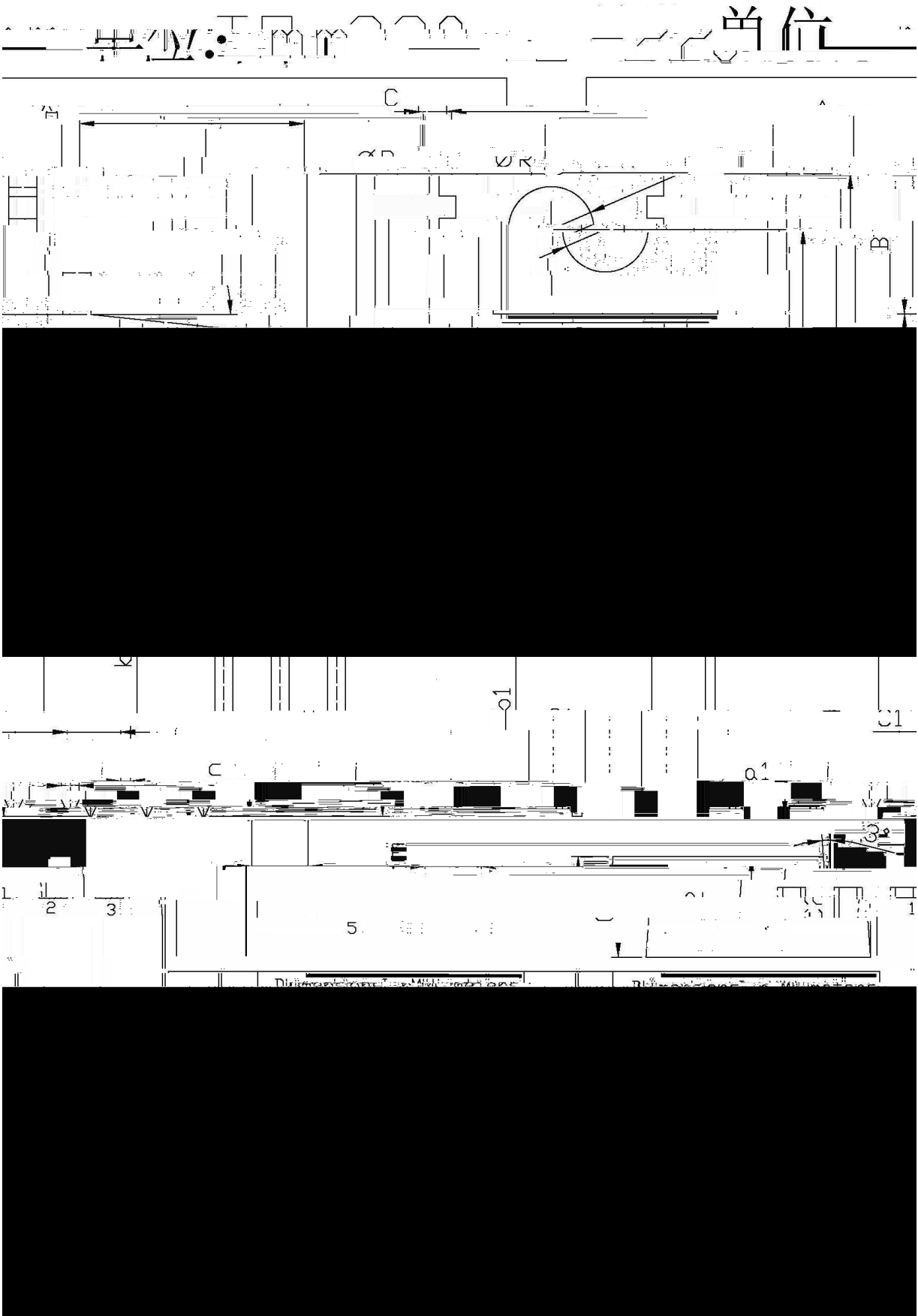
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
Average Rectified Forward Current	$I_{F(AV)}$	2×15	A
Non Repetitive Peak Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	4.6	/W
Junction and Storage Temperature Range	T_j T_{stg}	-40 +150	

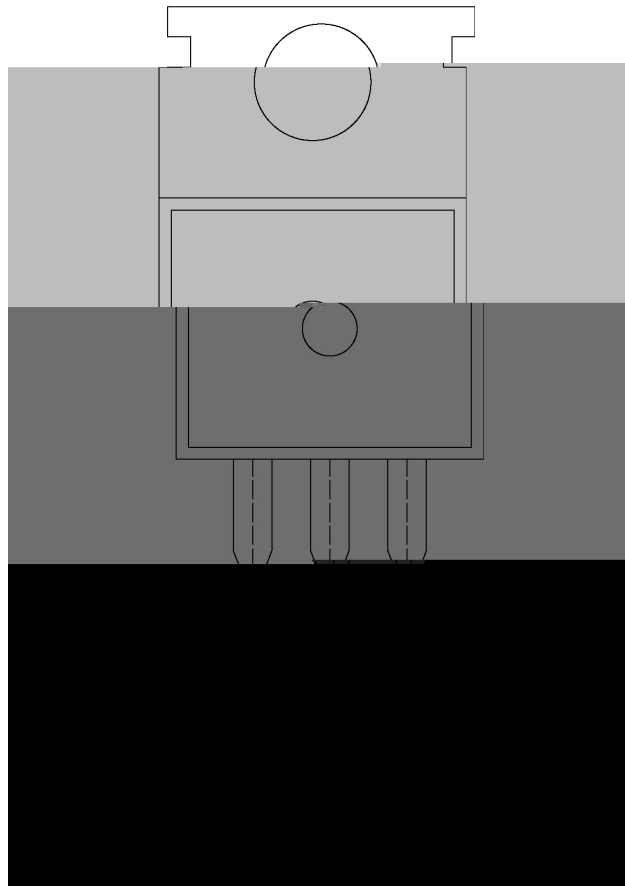
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Reverse Voltage	V_{BR}	$I_R=1mA(T_a=25^\circ C)$	200			V
Forward Voltage	V_F	$I_F=5A(T_a=25^\circ C)$		0.73	0.85	V
		$I_F=10A(T_a=25^\circ C)$		0.80	0.95	V
		$I_F=15A(T_a=25^\circ C)$		0.92	1.15	V
		$I_F=5A(T_a=125^\circ C)$		0.58		V
		$I_F=10A(T_a=125^\circ C)$		0.66		V
		$I_F=15A(T_a=125^\circ C)$		0.71	0.85	V
Instantaneous Reverse Current	I_R Note 1	$V_R=200V(T_a=25^\circ C)$		4	20	μA
		$V_R=200V(T_a=125^\circ C)$		5	10	mA

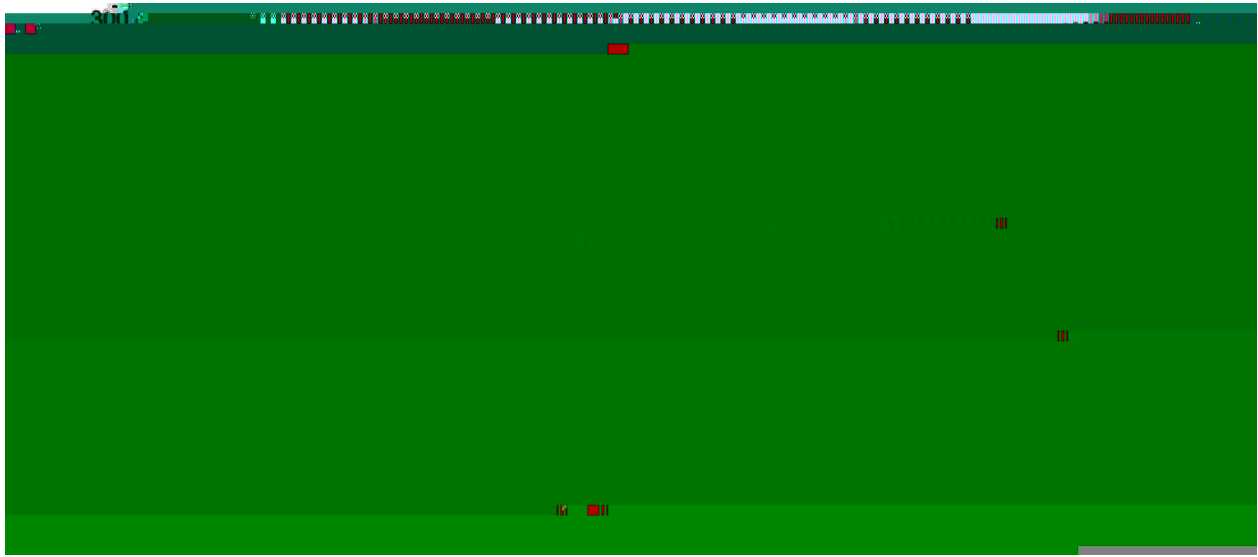
/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip









Note:

1 25 150 60 90sec;

1.Preheating:25~150